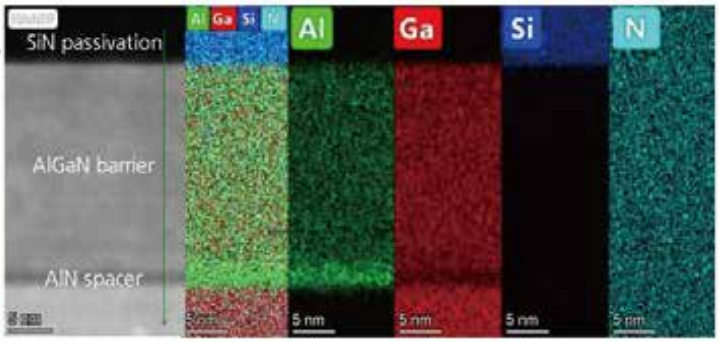
# 4 inch GaN on SiC Epiwafer Production Capacity

## Characterization Equipment for GaN on SiC RF Epitaxy

### ▶ Epi-structure



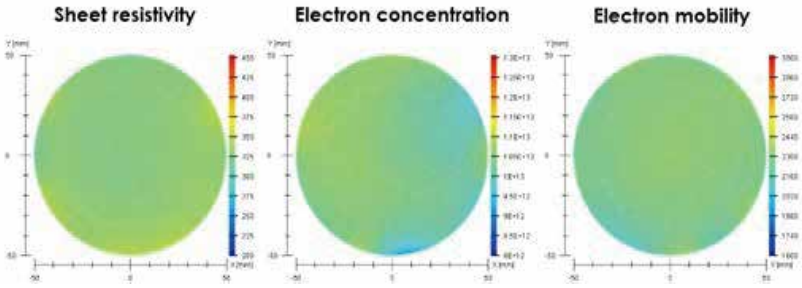

### ▶ TEM & EDS




### Veeco Propel

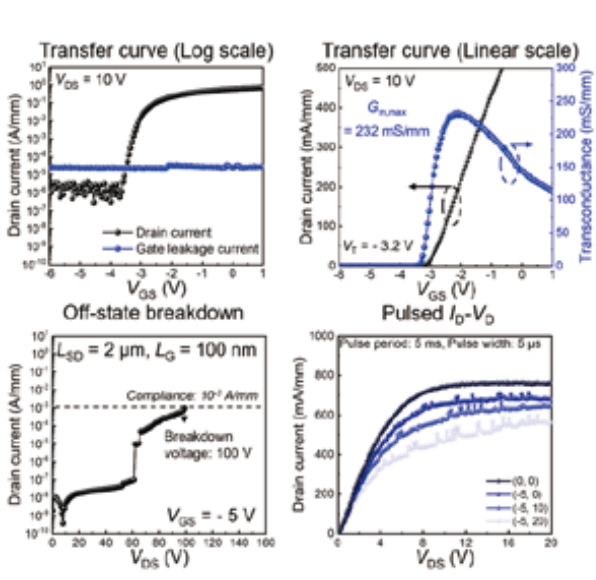


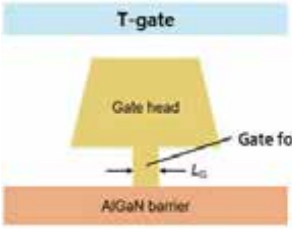
### ▶ LEI

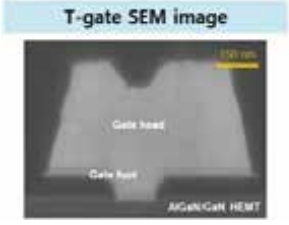



## ▶ Device information & Performance

- ◆ AlGaN barrier Al 22~28%, 15~25nm
- ◆ Sheet resistivity ~350Ω/□, Electron concentration ~1E13/cm$^2$, Electron mobility ~2100cm$^2$/Vs
- ◆ Vth : -3.1V, $G_{m,\,max}$ : 232mS/mm, $f_t$ : 44.9GHz, $f_{max}$ : 88.7GHz, Gain : 16.74dB





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